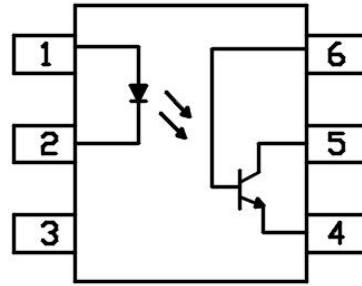
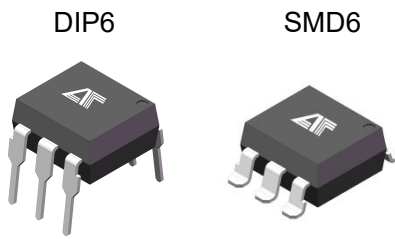


晶体管光耦 Photo Transistor

4N25

Product Data Sheet

AOTE DCC
RELEASE



Pin Configuration

- 1.Anode
- 2.Cathode
- 3.NC
- 4.Emitter
- 5.Collector
- 6.Base

◆ 封装逻辑原理图 Encapsulation logic schematic

4N25系列光耦采用高效光电转换技术，结合先进封装工艺，提供输入输出间的可靠隔离，支持DIP6、SMD6封装形式，适配多样化场景需求。

The 4N25 series optocoupler adopts high-efficiency photoelectric conversion technology and advanced packaging processes, providing reliable input-output isolation. It supports three package types DIP6、SMD6 to meet diverse application requirements.

◆ 产品特征Product features

- 输入-输出隔离电压 $V_{ios}=5000V_{rms}$
Input output isolation voltage: $V_{ios}=5000V_{rms}$
- 电流传输比CTR:10-100%范围: Current transmission ratio CTR: 10-100% range
- 集电极-发射极峰值击穿电压: $BV_{CEO}=70V$;
Collector emitter peak breakdown voltage $BV_{CEO}=70V$
- 爬电距离 $>7.0mm$;
Creepage distance $> 7.0mm$;
- 输入-输出绝缘距离 $>0.4mm$;
Input-Output insulation Thickness $> 0.4mm$
- 防潮等级 class1; MSL class1
- 产品符合 ROHS、REACH 及 HF 等环保法规要求;
The products comply with ROHS, REACH and HF;

◆ 应用领域 Applications

- 电源调节器：通常包括电压调节器、温度调节器、电流调节器等设备
Power regulator: It typically includes devices such as voltage regulators, temperature regulators, and current regulators.
- 数字逻辑输入：如传感器输入设备、编码器输入设备、计数器类输入设备。
Digital logic input: Sensor input devices, encoder input devices, counter-type input devices.
- 微处理器输入：如扫描仪、条码阅读机。
Microprocessor input: Like scanners, barcode readers



♦ 极限参数 Absolute Maximum Ratings (Ta =25°C)

参数 Parameter		符号 Symbol	额定值 Rating	单位 Unit
发射端 Input	正向电流 Forward Current	IF	60	mA
	峰值正向电流(1us, 脉冲) Peak forward current (1us, pulse)	IFP	1000	mA
	反向电压 Reverse Voltage	VR	6	V
	功耗 Power Dissipation	PD	100	mW
接收端 Output	集电极功耗 Collector Power Dissipation	PC	300	mW
	集电极电流 Collector Current	IC	100	mA
	集电极-基极电压 Collector-Base Voltage	VCBO	70	V
	集电极-发射极电压 Collector-Emitter Voltage	VCEO	30	V
	发射极-集电压 Emitter - Collector Voltage	VECO	7	V
隔离电压 Isolation Voltage		Viso	5000	Vrms
工作温度 Operating Temperature		Topr	-55 ~ +110	°C
存储温度 Storage Temperature		Tstg	-55 ~ +125	°C
焊接温度 Soldering Temperature		Tsol	260	°C

♦ 推荐操作条件 Recommended Operating Conditions

参数 Parameter	符号 Symbol	最小值 Min	最大值 Max.	单位 Unit
正向电流 Forward Current	IF	5	15	mA
集电极-发射极电压 Collector-Emitter Voltage	VCEO	5	70	V
集电极电流 Collector Current	IC	5	75	mA

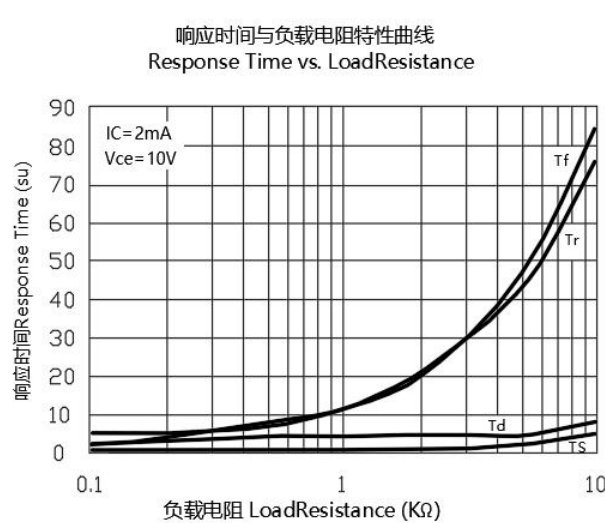
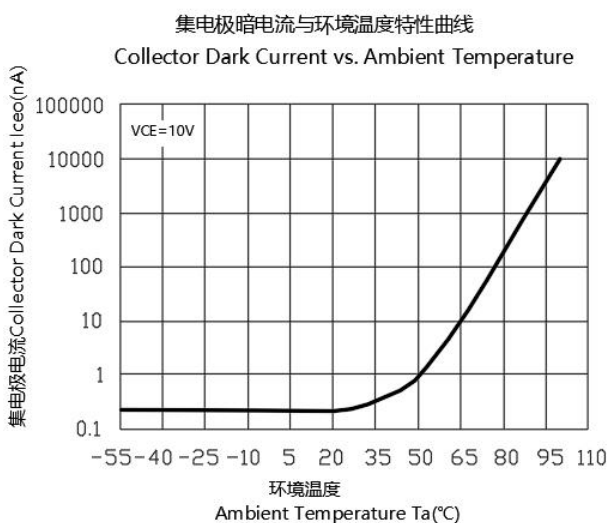
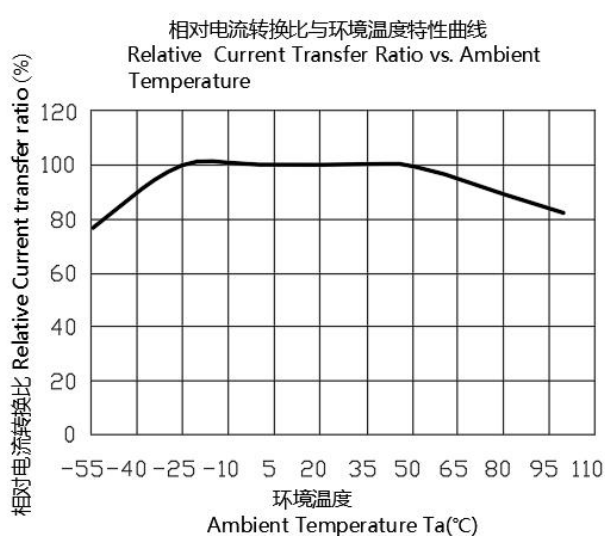
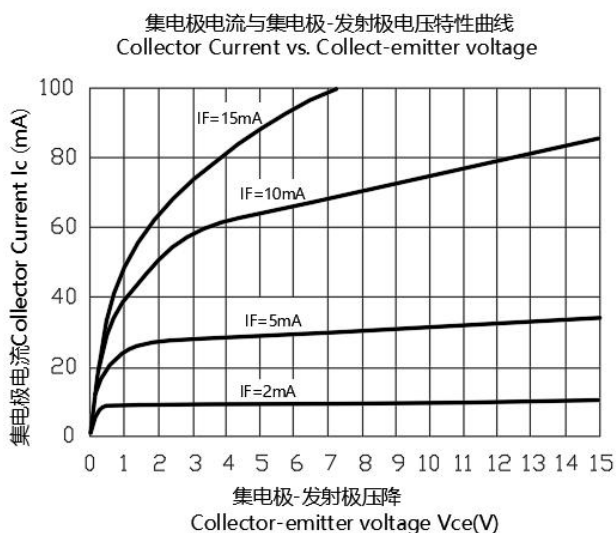
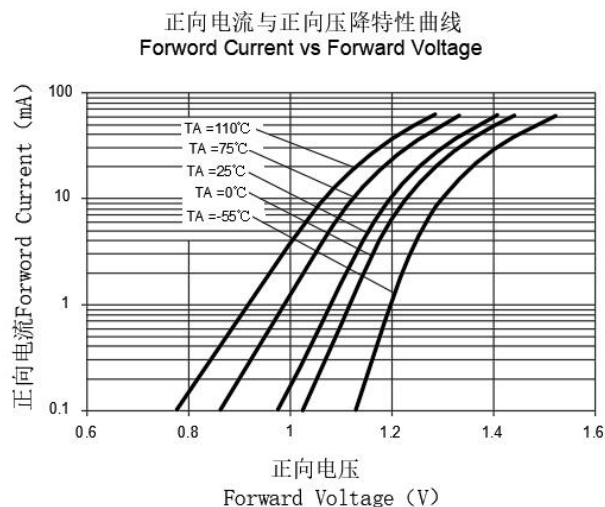
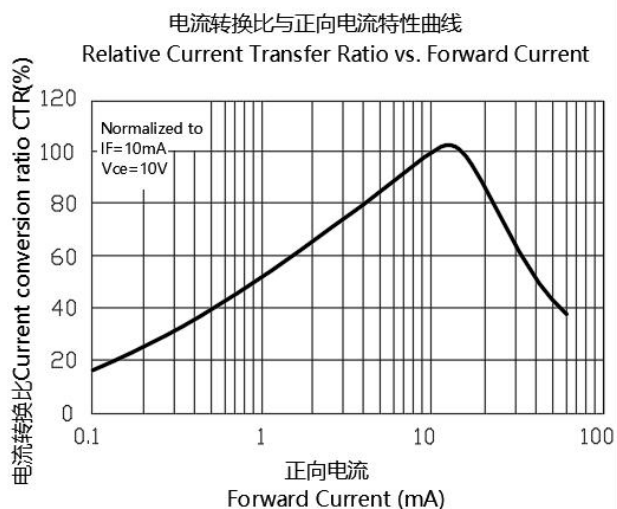
◆ 产品特性参数Product characteristic parameters (Ta =25°C)

参数 Parameter			符号 Symbol	条件 Condition	最小 Min	典型 Typ	最大 Max	单位 Unit
发射端 Input	正向电压 Forward Voltage		VF	IF =10mA	-	1.2	1.5	V
	反向电流 Reverse Current		IR	VR =3V	-	-	10	uA
	输入电容 Terminal Capacitance		Ct	V=0, F =1KHz	-	50	-	pF
接收端 Output	集电极暗电流 Collector Dark Current		ICEO	VCE=10V	-	-	50	nA
	集电极-基极击穿电压 Collector-Base Breakdown Voltage		BVCBO	IB =0.1mA, IF =0	70	-	-	V
	集电极-发射极击穿电压 Collector-Emitter Breakdown Voltage		BVCEO	IC =0.1mA, IF =0	30	-	-	V
	发射极-集电极击穿电压 Emitter-Collector Breakdown Voltage		BVECO	IE =0.01mA, IF =0	7	-	-	V
传输特性 Transfer Characteristics	电流传输比 Current Transfer Ratio	4N25、26、38	CTR*	IF=10mA, VCE=10V	20	-	-	%
		4N27、28			10	-	-	%
		4N35、36、37			100	-	-	%
	集电极-发射极饱和压降 Collector-Emitter Saturation Voltage		VCE(sat)	IF=50mA, IC =2mA	-	-	0.3	V
	隔离电阻 Isolation Resistance		RISO	DC=500V 40 ~60%R.H.	5x10 ¹⁰	1x10 ¹¹	-	Ω
	隔离电容 Isolation capacitance		CISO	V=0, F=1MHz	-	1	2.5	pF
	上升时间 Rise Time		Tr	VCE=10V, IC =2mA, RL =100Ω	-	4	-	μs
	下降时间 Fall Time		Tf		-	3	-	μs

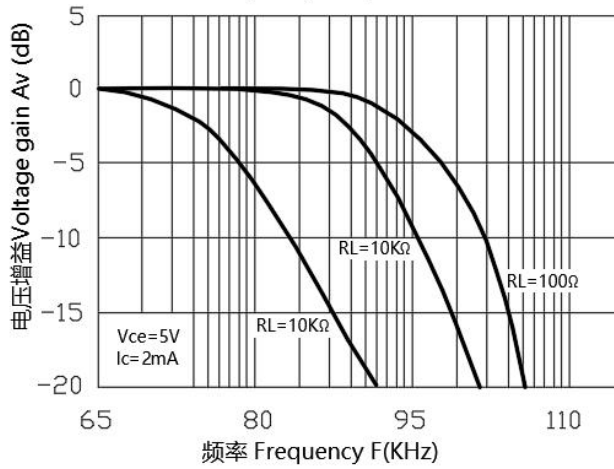
注 电流传输比= $I_C/I_F \times 100\%$ 。

Note*: CTR= $I_C/I_F \times 100\%$ 。

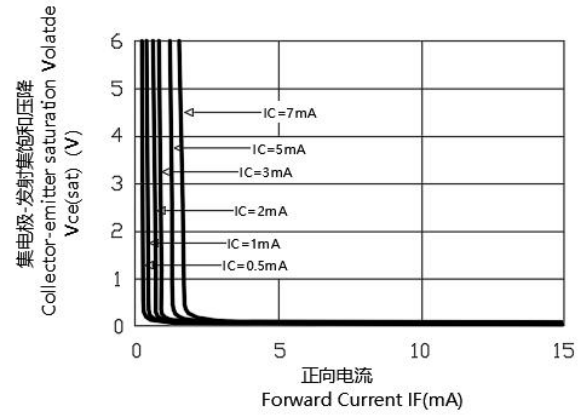
◆ 电性特性曲线Electrical characteristic curve($T_a = 25^\circ\text{C}$)



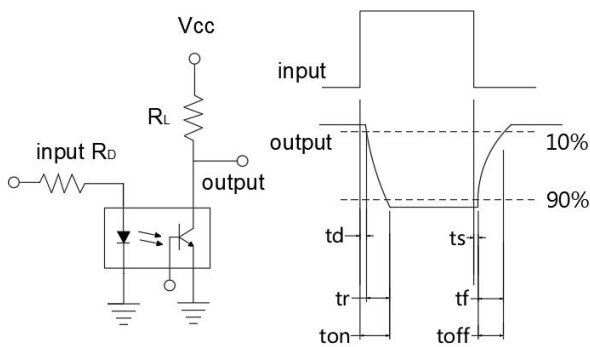
频率响应特性曲线
Frequency Response



集电极-发射极饱和压降与正向电流特性曲线
Collect-emitter Saturation Voltage vs.
Forward Current

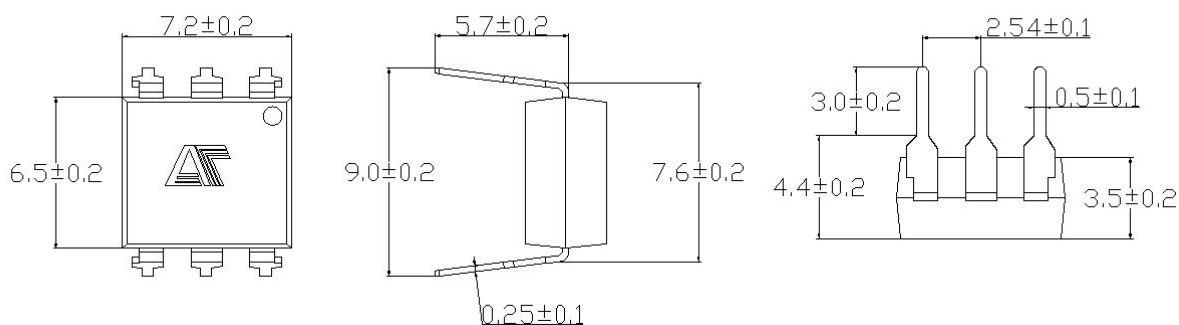


响应时间测试电路
Test Circuit for Response Time

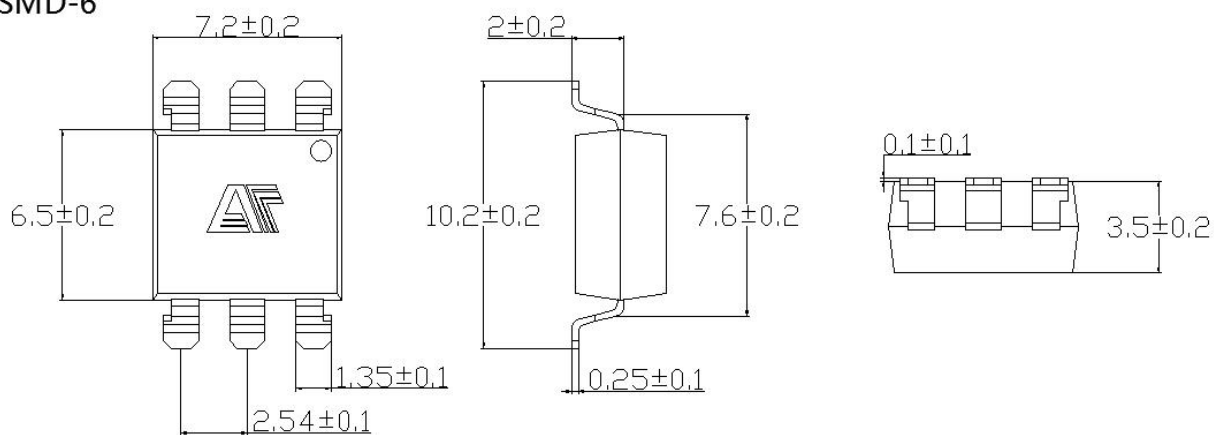


◆ 外形尺寸Overall dimension

DIP6

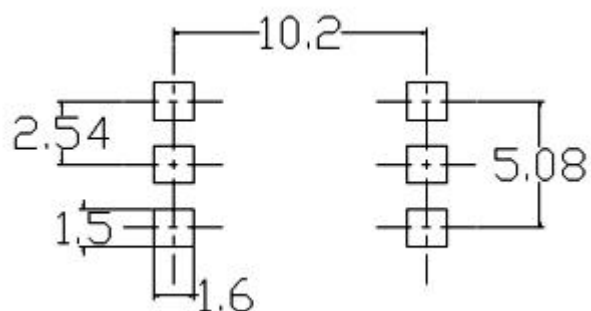


SMD-6



推荐焊盘:

Recommended



单位: mm

◆ 印字信息 Marking Information

- 印字中 “  ” 为奥特品牌LOGO
“  ” denotes LOGO
- 印字中的 “XX” 代表产品分档：25, 26, 27,28,35,36,37,38
“XX” denotes the classification: 25, 26, 27,28,35,36,37,38
- 印字中 “Y” 代表年份；A(2018),B(2019),C(2020).....
“Y” denotes YEAR: A(2018), B(2019), C(2020).....
- 印字中 “WW” 代表周号
“WW” denotes Week' s number
- 印字中 “E” 代表内部代码
“E” denotes Internal code
- 印字中的 “H” 代表无卤
“H” denotes Halogen-free

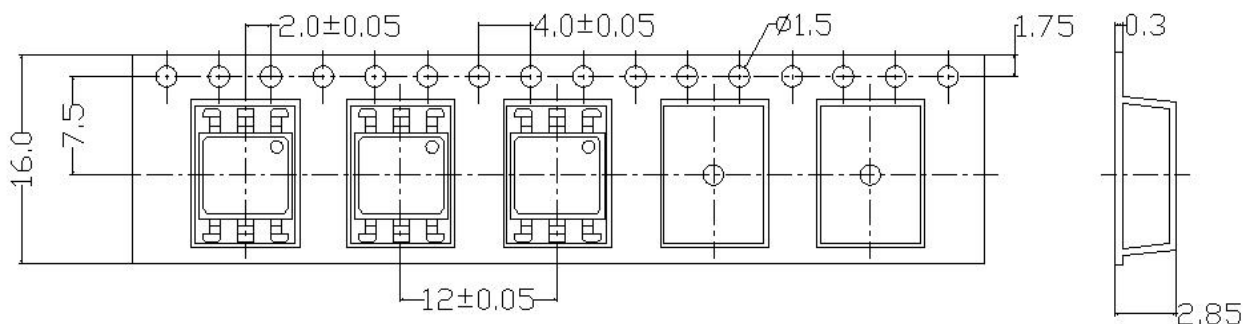
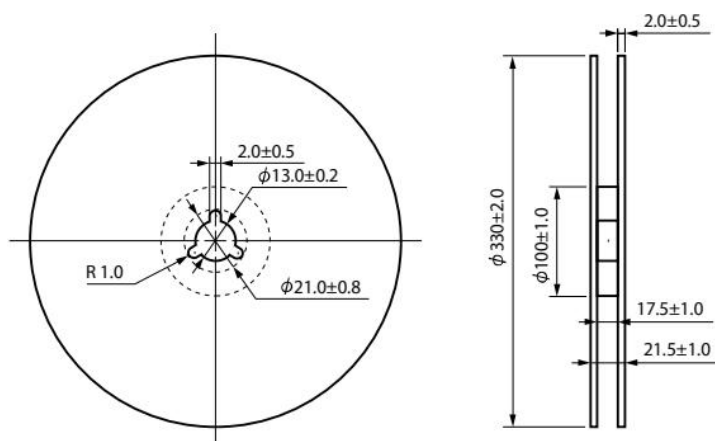


◆ 包装packing

封装形式	包装方式	盘数量	盒数量	箱数量	静电袋规格	盒规格	箱(双瓦楞)规格	备注
SMD6	卷盘 ($\phi 330$ mm 蓝盘)	1000 只/盘	2 盘/盒	10 盒/箱	450*390* 0.1mm	340*60* 340mm	620*360* 365mm	首尾端空至少 200mm
DIP6	管装 (500*12*11mm)	65 只/管	50 管/盒	10 盒/箱	不适用	525*128* 56mm	535*275* 300mm	每管使用蓝白胶 塞, 方向须一致
Package Type	Packing Form	Quantity per Reel	Quantity per Box	Quantity per Carton	Antistatic Bag Specification	Box Specification	Carton Specification	Note
SMD6	Reel ($\phi 330$ mm Blue)	1000 pcs/reel	2 reels/box	10 boxes/ctn	450*390* 0.1mm	340*60* 340mm	620*360* 365mm	Guard band 200mm min.
DIP6	Tube (500*12*11mm)	65 pcs /tube	50 tubes/box	10 boxes/ctn	NA	525*128* 56mm	535*275* 300mm	Endplug (blue) and Endplug (white) keep the direction

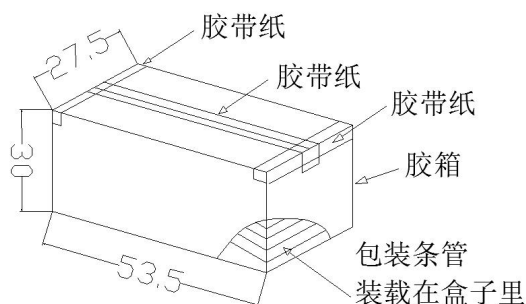
• 编带包装 Tape & Reel

- 1) 每卷数量: 1000 只;
Qty/reel: 1000 pcs.
- 2) 每箱数量: 20000 只;
Qty/ctn: 20000 pcs.
- 3) 内包装: 每盒 2 盘;
Inner packing: 2 reels/box.
- 4) 示意图 Schematic:



• 管条包装 Tape & Tube

- 1) 每管数量: 50 只;
Qty/Tube 50 pcs.
- 2) 每箱数量: 32500 只;
Qty/ctn: 32500 pcs.
- 3) 内包装: 每盒 50 管;
Inner packing: 50 Tube/box.
- 4) 示意图 Schematic:

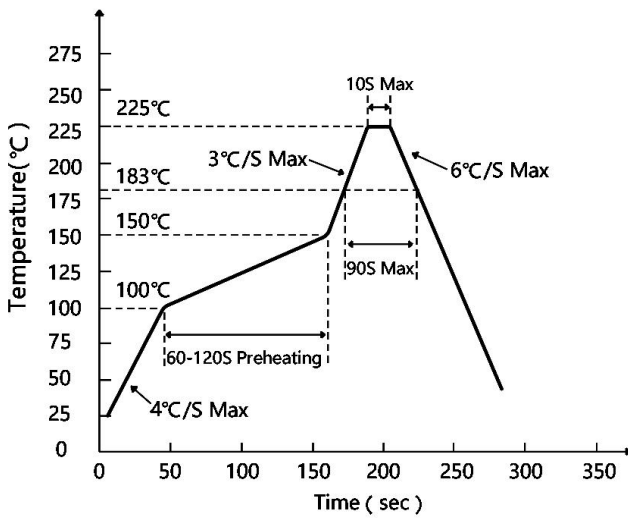


单位: mm

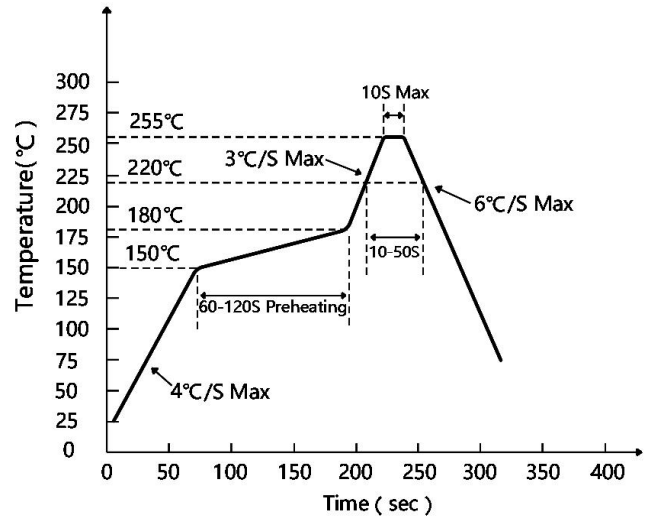
◆ 可靠性测试 Reliability Test Items And Conditions

实验项目 Test Items	参考标准 Reference	实验条件 Test Conditions	时间 Time	样品数 Quantity	判据 Criterion
可焊性 Solderability	JESD22-B102	Tsol= (245±5) °C, t=5s;	1 次1 times	22	0/22
耐焊接热Resistance to Soldering Heat	JESD22-A106	Tsol= (260±5) °C, t=10s	3 次3 times	22	0/22
静电放电 ESD-HBM	JESD22-A114	Ta=25°C, HBM (2000V)	正反各 3 次 P&N 3 times	10	0/10
高温贮存High emperature Storage	JESD22-A103	Ta=125°C	1000h	22	0/22
低温贮存 Low Temperature Storage	JESD22-A119	Ta= -55°C	1000h	22	0/22
冷热冲击 Thermal Shock	JESD22-A104	-55°C(15min)←→ 125°C(15min)	循环 300 次 300 cycles	22	0/22
常温寿命试验 Lifespan Test	JESD22-A108	Ta=25°C, IF=50mA , Vcc=5V	1000h	22	0/22
高温寿命试验 DC Operating Life	JESD22-A108	Ta=110°C, IF=20mA , Vcc=5V	1000h	76	0/76
高温高湿偏压 High Temperature High Humidity bias Voltage	JESD22-A101	Ta =85°C , RH=85% IF=0mA , VCE=64V	1000h	22	0/22
高温偏压 High Temperature bias Voltage	JESD22-A108	Ta =110°C , IF=0mA , VCE=80V	1000h	22	0/22
高压蒸汽试验 High pressure steam test	JESD22-A102	P=15PSIG , 121°C, 100%RH	96h	22	0/22

◆ 回流焊温度曲线图 Solder Reflow Profile

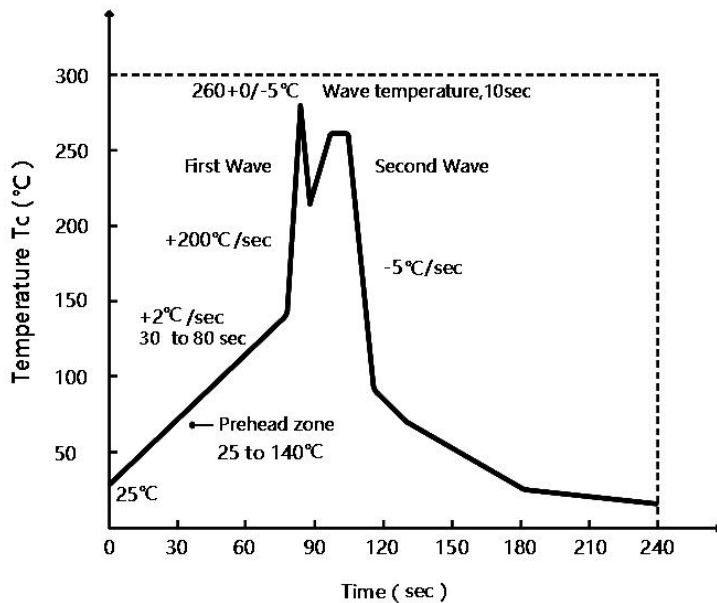


有铅制程 Lead Process



无铅制程 Lead Process

◆ 波峰焊温度曲线图 Wave Soldering Profile



◆ 手工烙铁焊接 Soldering with hand soldering iron

A. 手工烙铁焊仅用于产品返修或样品测试;

Hand soldering iron is only used for product rework or sample testing;

B. 手工烙铁焊要求: 温度 350°C ± 5°C, 时间 ≤ 3s.

Hand soldering iron requirements: Temperature: 350°C ± 5°C, within 3s.

◆ 注意 Attention

- 奥特半导体实施动态技术迭代机制，产品规格可能随工艺升级调整，最新技术参数以官网发布版本为准。

AOTE implements dynamic technical updates. Specifications are subject to change. Refer to the official website for the latest version.

- 用户需严格遵循本规格书限定的操作条件，因超范围使用（包括但不限于过载、高温、非兼容电路设计）导致的器件失效，不在质量保证范围内。

Users must strictly adhere to specified conditions. Failures caused by misuse (overload, high temperature, incompatible circuits) are excluded from warranty.

- 医疗设备、工业控制等关键场景应用前，需联系技术支持获取定制化验证方案。

Contact technical support for customized validation in critical applications (medical devices, industrial control).

- 本文档有效期至2025年12月31日，后续更新将通过官网公告推送。

This document is valid until Dec 31, 2025. Updates will be notified on the official website.

- 如需对技术参数或应用方案进行进一步确认，欢迎通过以下渠道获取官方支持：

For further clarification on technical specifications or application solutions, please contact us through official channels: